

# N-channel TrenchMOS standard level FET Rev. 3 — 23 February 2011

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 185 °C rating

### 1.3 Applications

- 12 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

### 1.4 Quick reference data

Table 1.	Quick reference	data					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 185 °C		-	-	30	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u>	-	-	75	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	167	W
Static cha	aracteristics						
$R_{DSon}$	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>		-	5.9	7	mΩ



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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 75 \text{ A};  V_{sup} \leq 30 \text{ V}; \\ R_{GS} &= 50  \Omega;  V_{GS} = 10 \text{ V}; \\ T_{j(init)} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	329	mJ
Dynamic ch	naracteristics					
Q <sub>GD</sub>	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 24 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 13</u>	-	10	-	nC

[1] Continuous current is limited by package.

## 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT428 (DPAK)	

[1] It is not possible to make connection to pin 2.

### 3. Ordering information

#### Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK7207-30B	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

## 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

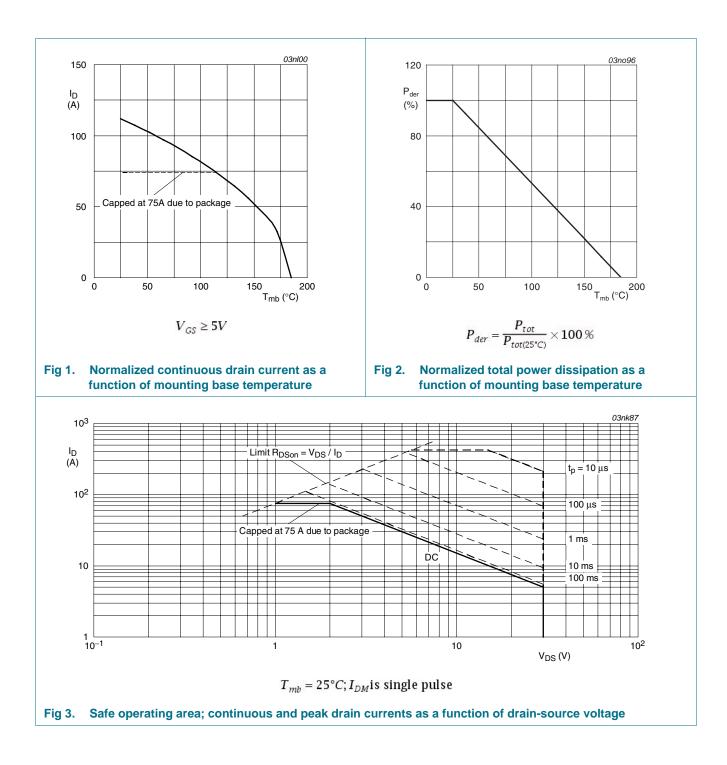
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 185 °C	-	30	V
V <sub>DGR</sub>	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	30	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
	drain current	$V_{GS}$ = 10 V; T <sub>j</sub> = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u> _	112	А
		$T_{mb}$ = 100 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	[2] _	75	А
		$V_{GS} = 10 \text{ V}; \text{ T}_{j} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$	<u>[2]</u> _	75	А
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 µs; T <sub>j</sub> = 25 °C; see <u>Figure 3</u>	-	449	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	167	W
T <sub>stg</sub>	storage temperature		-55	185	°C
Tj	junction temperature		-55	185	°C
Source-drain	diode				
Is	source current	T <sub>mb</sub> = 25 °C	[2]	75	А
			<u>[1]</u> _	112	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	449	А
Avalanche ru	ggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 75 A; V <sub>sup</sub> ≤ 30 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped	-	329	mJ

[1] Current is limited by power dissipation chip rating.

[2] Continuous current is limited by package.

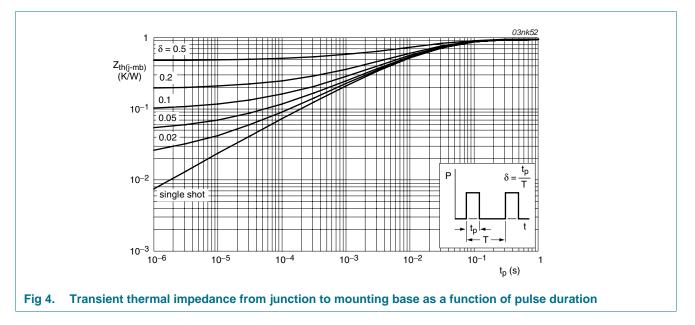
# BUK7207-30B

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### 5. Thermal characteristics

Parameter	Conditions	Min	Тур	Max	Unit
thermal resistance from junction to mounting base	see Figure 4	-	-	0.95	K/W
thermal resistance from junction to ambient		-	71.4	-	K/W
	thermal resistance from junction to mounting base	thermal resistance from junction to mounting see Figure 4 base	thermal resistance from junction to mounting see Figure 4 - base	thermal resistance from junction to mounting see Figure 4 base	thermal resistance from junction to mounting see <u>Figure 4</u> 0.95 base



#### Table 5. Thermal characteristics

## 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	30	-	-	V
	breakdown voltage	I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u>	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 185 \text{ °C};$ see <u>Figure 10</u>	0.9	-	-	V
	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <u>Figure 10</u>	-	-	4.4	V	
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 185 \text{ °C}$	-	-	500	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 185 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	13.3	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	5.9	7	mΩ
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{12}$	-	34	-	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 24 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> 25 °C; see <u>Figure 13</u>	-	8	-	nC
Q <sub>GD</sub>	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{12}$	-	10	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	1684	2245	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	625	750	pF
C <sub>rss</sub>	reverse transfer capacitance		-	249	314	pF
t <sub>d(on)</sub>	turn-on delay time		-	14	-	ns
t <sub>r</sub>	rise time		-	85	-	ns
d(off)	turn-off delay time	$V_{DS} = 25 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	55	-	ns
<sup>l</sup> f	fall time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	76	-	ns
ЬD	internal drain inductance	measured from drain to centre of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	measured from source lead to source bond pad; $T_i = 25 \text{ °C}$	-	7.5	-	nH

Symbol

Source-drain diode

# BUK7207-30B

Max

Unit

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Тур

Min

D	source-drain voltage	$I_S = 20 \text{ A}; V_{GS} = 0$ see <u>Figure 15</u>	v, 1j – 25° O,			1.2	V
	reverse recovery time	$I_{S} = 20 \text{ A}; \text{ d}I_{S}/\text{d}t = -$		-	43	-	ns
	recovered charge	V <sub>GS</sub> = -10 V; V <sub>DS</sub> =	25 V; T <sub>j</sub> = 25 °C	-	20	-	nC
400		03nk84	10			03nk83	
400 I <sub>D</sub> 20	10 Lab	el is V <sub>GS</sub> (V)	12 R <sub>DSon</sub>				
(Ā) 14	9.5		(mΩ)				
<sup>300 –</sup> 12	9 8.5		10				
200	8						
200	7 6.5		8				
100 —	6		6				
	5.5						
٥K	4.5		4				
Č A	0 1 0	a 1a		10	. –	20	)
0	2 4 6	8 10 V <sub>DS</sub> (V)	5	10	15 V	′ <sub>GS</sub> (V)	
0	$T_j = 25^{\circ}C; t_p = 300\mu$	V <sub>DS</sub> (V)	5		$I_D^{15}$	/ <sub>GS</sub> (V)	
ig 5. Outj		V <sub>DS</sub> (V) µs n current as a	5 Fig 6. Drain-sc		$C; I_D = 25A$	r <sub>GS</sub> (V) Ince as a f	
ig 5. Outj func	$T_j = 25^{\circ}C; t_p = 300p$	V <sub>DS</sub> (V) µs n current as a	5 Fig 6. Drain-so of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	r <sub>GS</sub> (V) Ince as a f	
ig 5. Out func	$T_j = 25^{\circ}C; t_p = 300p$	V <sub>DS</sub> (V) µs n current as a tage; typical values	5 Fig 6. Drain-sc of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	( <sub>GS</sub> (V) Ice as a f Values	
ig 5. Out <sub>1</sub> func	$T_j = 25^{\circ}C; t_p = 300p$	V <sub>DS</sub> (V) µs n current as a tage; typical values	5 Fig 6. Drain-so of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	( <sub>GS</sub> (V) Ice as a f Values	
ig 5. Out func	$T_j = 25^{\circ}C; t_p = 300\mu$ put characteristics: drain stion of drain-source volt	V <sub>DS</sub> (V) <i>µs</i> n current as a tage; typical values	5 Fig 6. Drain-sc of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	( <sub>GS</sub> (V) Ice as a f Values	
ig 5. Out <sub>1</sub> func	$T_j = 25^{\circ}C; t_p = 300\mu$ put characteristics: drain stion of drain-source volt	V <sub>DS</sub> (V) <i>µs</i> n current as a tage; typical values	5 Fig 6. Drain-sc of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	( <sub>GS</sub> (V) Ice as a f Values	
ig 5. Out func $10^{-1}$ $I_D$ (A) $10^{-2}$	$T_j = 25^{\circ}C; t_p = 300\mu$ put characteristics: drain stion of drain-source volt	V <sub>DS</sub> (V) <i>µs</i> n current as a tage; typical values	5 Fig 6. Drain-sc of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	( <sub>GS</sub> (V) Ice as a f Values	
ig 5. Outj func $10^{-1}$ $I_D$ (A) $10^{-2}$ $10^{-3}$	$T_j = 25^{\circ}C; t_p = 300\mu$ put characteristics: drain stion of drain-source volt	V <sub>DS</sub> (V) <i>µs</i> n current as a tage; typical values	5 Fig 6. Drain-sc of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	( <sub>GS</sub> (V) Ice as a f Values	
ig 5. Out func $10^{-1}$ $I_D$ (A) $10^{-2}$	$T_j = 25^{\circ}C; t_p = 300\mu$ put characteristics: drain stion of drain-source volt	V <sub>DS</sub> (V) <i>µs</i> n current as a tage; typical values	5 Fig 6. Drain-sc of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	( <sub>GS</sub> (V) Ice as a f Values	
$\begin{array}{c} 10^{-1} \\ I_D \\ (A) \\ 10^{-2} \\ 10^{-3} \end{array}$	$T_j = 25^{\circ}C; t_p = 300\mu$ put characteristics: drain stion of drain-source volt	V <sub>DS</sub> (V) <i>µs</i> n current as a tage; typical values	5 Fig 6. Drain-sc of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	( <sub>GS</sub> (V) Ice as a f Values	
ig 5. Out function $I_D^{10^{-1}}$ (A) $I_D^{-2}$ $I_D^{-3}$ $I_D^{-4}$ $I_D^{-5}$	$T_j = 25^{\circ}C; t_p = 300\mu$ put characteristics: drain stion of drain-source volt	V <sub>DS</sub> (V) <i>µs</i> n current as a tage; typical values	5 Fig 6. Drain-sc of gate-s	$T_j = 25^{\circ}C$	$C; I_D = 25A$	( <sub>GS</sub> (V) Ice as a f Values	
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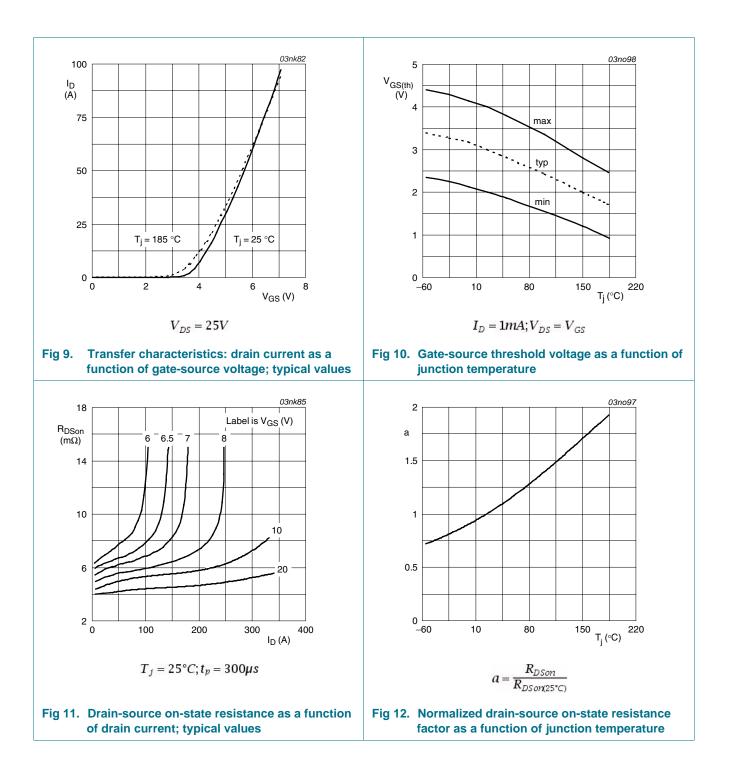
#### Table 6. Characteristics ... continued

Parameter

Conditions

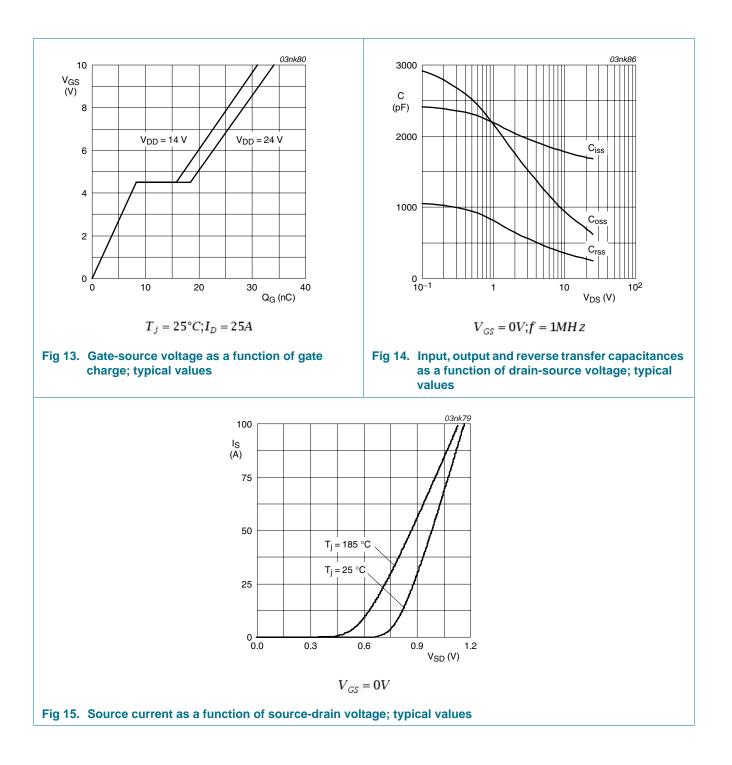
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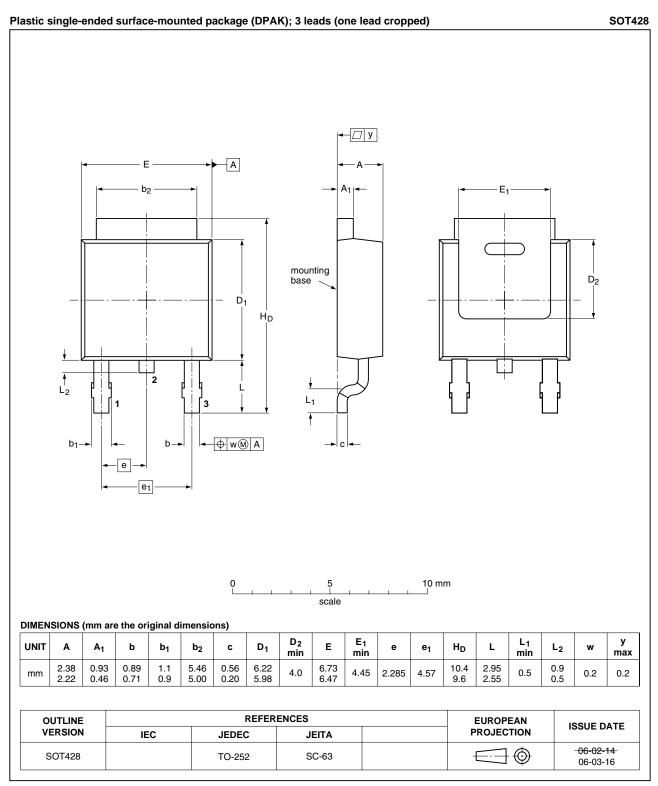
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### 7. Package outline



#### Fig 16. Package outline SOT428 (DPAK)

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# 8. Revision history

Table 7.Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7207-30B v.3	20110223	Product data sheet	-	BUK7207_30B-02
Modifications:	of NXP Semic	this data sheet has been rec conductors. we been adapted to the new		
BUK7207_30B-02 (9397 750 12227)	20040122	Product data	-	BUK7207_30B-01

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#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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